

General Description

The GreenMOS[®] high voltage MOSFET utilizes charge balance technology to achieve outstanding low on-resistance and lower gate charge. It is engineered to minimize conduction loss, provide superior switching performance and robust avalanche capability.

The GreenMOS[®] SuperSi series is based on Oriental Semiconductor's unique device design to achieve extremely fast switching characteristics. It is the perfect replacement for the Gallium Nitride (GaN) device in high frequency operations with better ruggedness and cost. It is targeted to meet the most aggressive efficiency standards of power supply systems by pushing both performance and power density to extreme limits.

Features

- Low $R_{DS(ON)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Easy to design in




Applications

- PD charger
- Large screen display
- Telecom power
- Server power

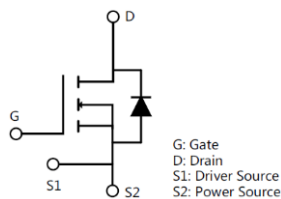
Key Performance Parameters

Parameter	Value	Unit
$V_{DS, min} @ T_{j(max)}$	700	V
$I_D, pulse$	54	A
$R_{DS(ON), max} @ V_{GS}=10V$	240	m Ω
Q_g	13.1	nC

Marking Information

Product Name	Package	Marking
OSS65R240JF	PDFN 8x8	OSS65R240J

Package & Pin Information



Absolute Maximum Ratings at $T_j=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Gate-source voltage	V_{GS}	± 30	V
Continuous drain current ¹⁾ , $T_C=25^\circ\text{C}$	I_D	18	A
Continuous drain current ¹⁾ , $T_C=100^\circ\text{C}$		11.5	
Pulsed drain current ²⁾ , $T_C=25^\circ\text{C}$	$I_{D, pulse}$	54	A
Continuous diode forward current ¹⁾ , $T_C=25^\circ\text{C}$	I_S	18	A
Diode pulsed current ²⁾ , $T_C=25^\circ\text{C}$	$I_{S, pulse}$	54	A
Power dissipation ³⁾ , $T_C=25^\circ\text{C}$	P_D	110	W
Single pulsed avalanche energy ⁵⁾	E_{AS}	212	mJ
MOSFET dv/dt ruggedness, $V_{DS}=0\dots 480\text{ V}$	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS}=0\dots 480\text{ V}$, $I_{SD}\leq I_D$	dv/dt	15	V/ns
Operation and storage temperature	T_{stg}, T_j	-55 to 150	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal resistance, junction-case	$R_{\theta JC}$	1.14	$^\circ\text{C/W}$
Thermal resistance, junction-ambient ⁴⁾	$R_{\theta JA}$	62	$^\circ\text{C/W}$

Electrical Characteristics at $T_j=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Drain-source breakdown voltage	BV_{DSS}	650			V	$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$
		700				$V_{GS}=0\text{ V}$, $I_D=250\ \mu\text{A}$, $T_j=150^\circ\text{C}$
Gate threshold voltage	$V_{GS(th)}$	2.9		3.9	V	$V_{DS}=V_{GS}$, $I_D=250\ \mu\text{A}$
Drain-source on-state resistance	$R_{DS(on)}$		0.19	0.24	Ω	$V_{GS}=10\text{ V}$, $I_D=5.6\text{ A}$
			0.42			$V_{GS}=10\text{ V}$, $I_D=5.6\text{ A}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}			100	nA	$V_{GS}=30\text{ V}$
				-100		$V_{GS}=-30\text{ V}$
Drain-source leakage current	I_{DSS}			1	μA	$V_{DS}=650\text{ V}$, $V_{GS}=0\text{ V}$
Gate resistance	R_G		23		Ω	f=1 MHz, Open drain

Dynamic Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Input capacitance	C_{iss}		673		pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=100\text{ kHz}$
Output capacitance	C_{oss}		81		pF	
Reverse transfer capacitance	C_{rss}		3.9		pF	
Effective output capacitance, energy related	$C_{o(er)}$		49		pF	$V_{GS} = 0\text{ V}$, $V_{DS} = 0\text{V-}400\text{V}$
Effective output capacitance, time related	$C_{o(tr)}$		254		pF	
Turn-on delay time	$t_{d(on)}$		24.8		ns	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $R_G=2\ \Omega$, $I_D=10\text{ A}$
Rise time	t_r		19.4		ns	
Turn-off delay time	$t_{d(off)}$		51.4		ns	
Fall time	t_f		17.2		ns	

Gate Charge Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Total gate charge	Q_g		13.1		nC	$V_{GS}=10\text{ V}$, $V_{DS}=400\text{ V}$, $I_D=10\text{ A}$
Gate-source charge	Q_{gs}		3.7		nC	
Gate-drain charge	Q_{gd}		4.9		nC	
Gate plateau voltage	$V_{plateau}$		5.7		V	

Body Diode Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test condition
Diode forward voltage	V_{SD}			1.3	V	$I_S=18\text{ A}$, $V_{GS}=0\text{ V}$
Reverse recovery time	t_{rr}		332		ns	$V_R=400\text{ V}$, $I_S=10\text{ A}$, $di/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}		3.9		μC	
Peak reverse recovery current	I_{rrm}		22.5		A	

Note

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25\text{ }^\circ\text{C}$.
- 5) $V_{DD}=100\text{ V}$, $V_{GS}=10\text{ V}$, $L=80\text{ mH}$, starting $T_j=25\text{ }^\circ\text{C}$.

Electrical Characteristics Diagrams

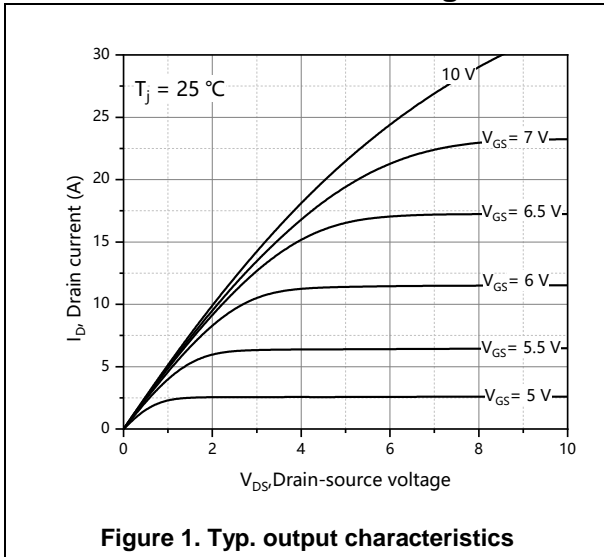


Figure 1. Typ. output characteristics

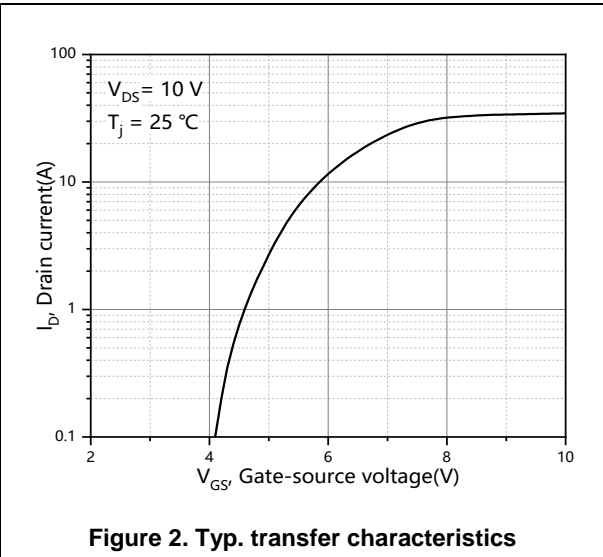


Figure 2. Typ. transfer characteristics

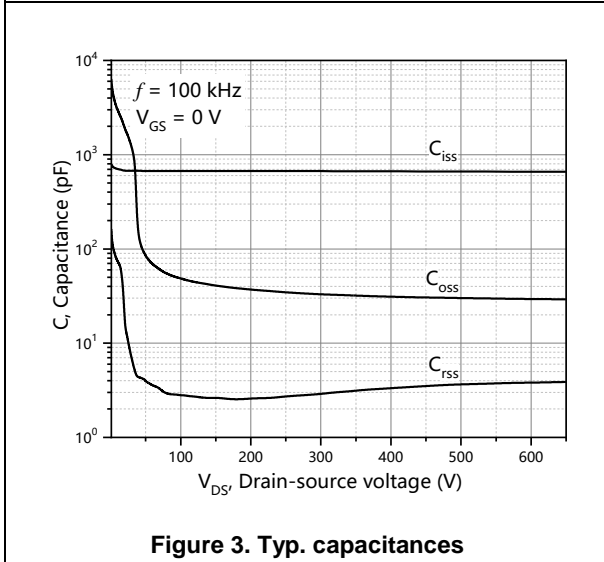


Figure 3. Typ. capacitances

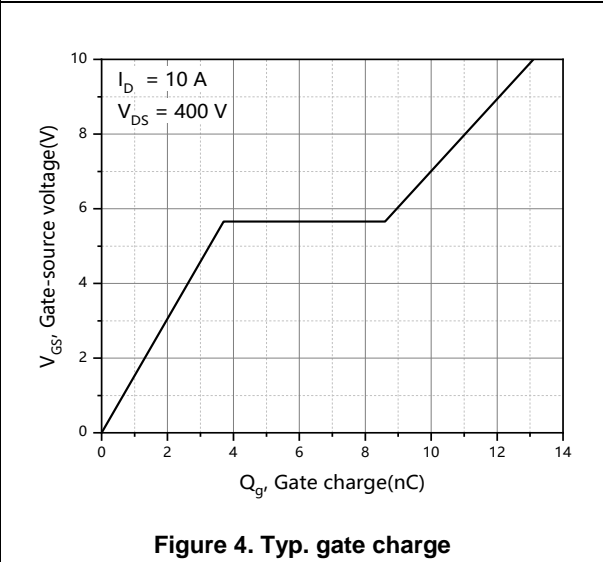


Figure 4. Typ. gate charge

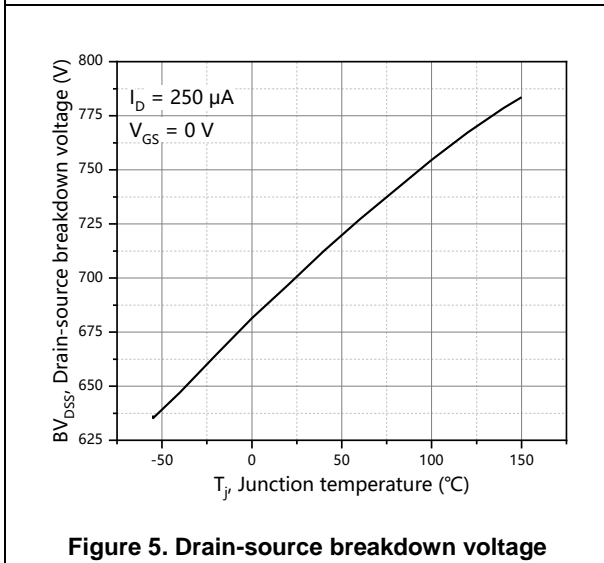


Figure 5. Drain-source breakdown voltage

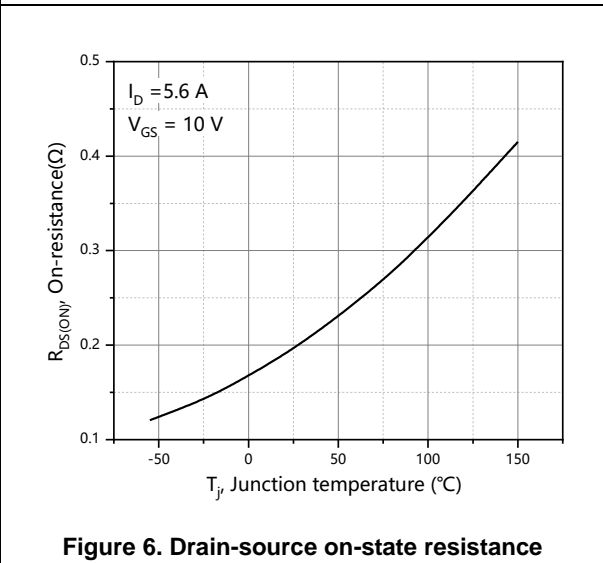
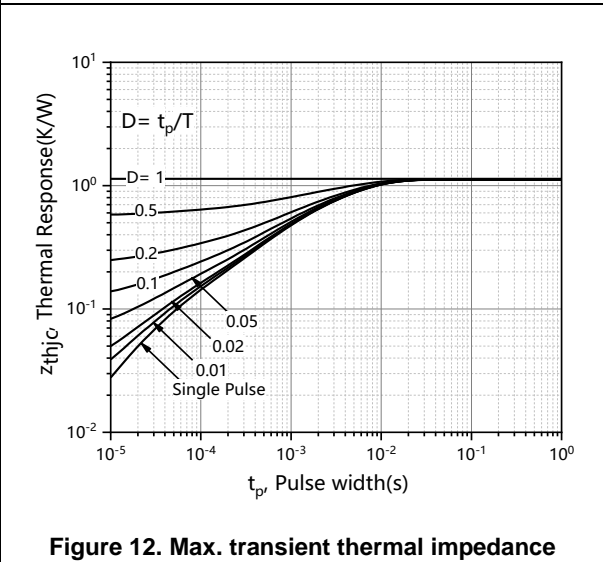
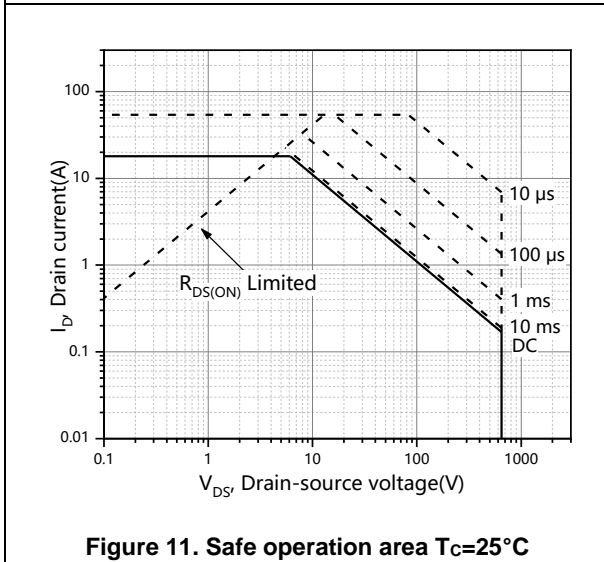
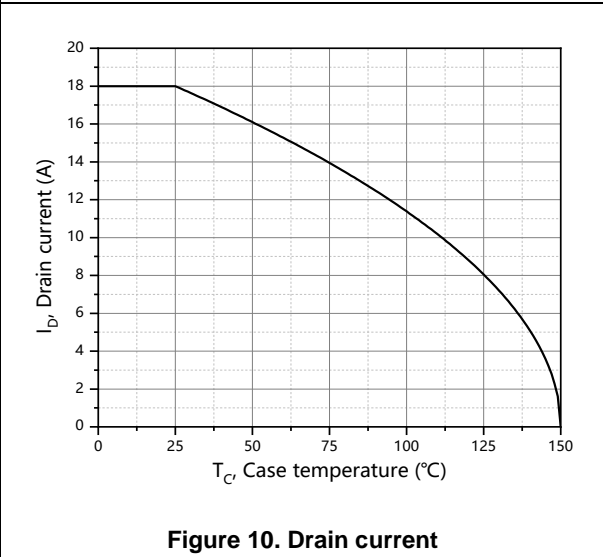
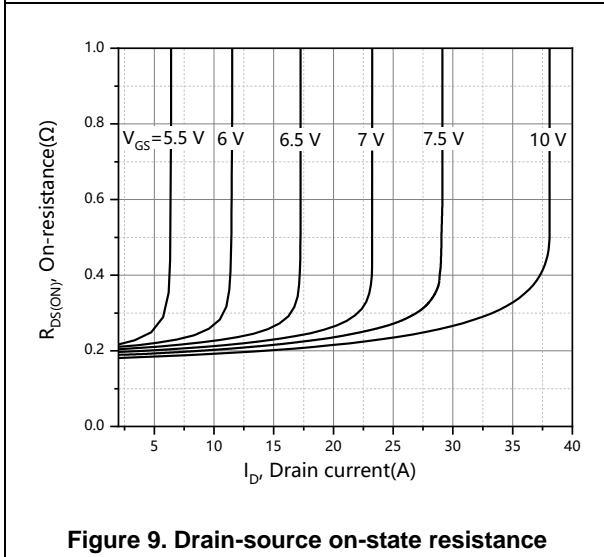
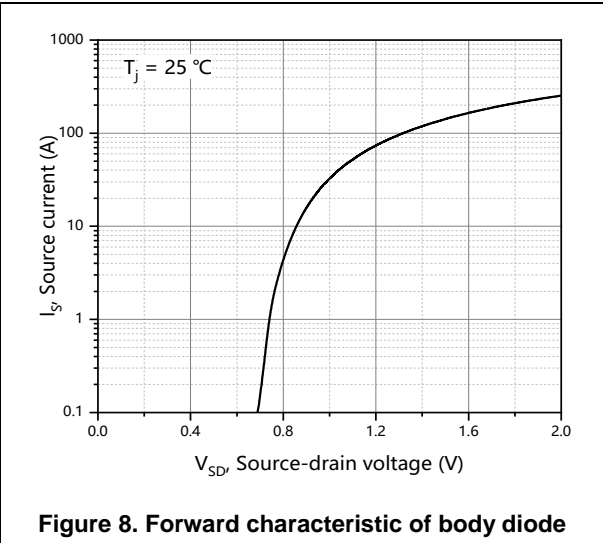
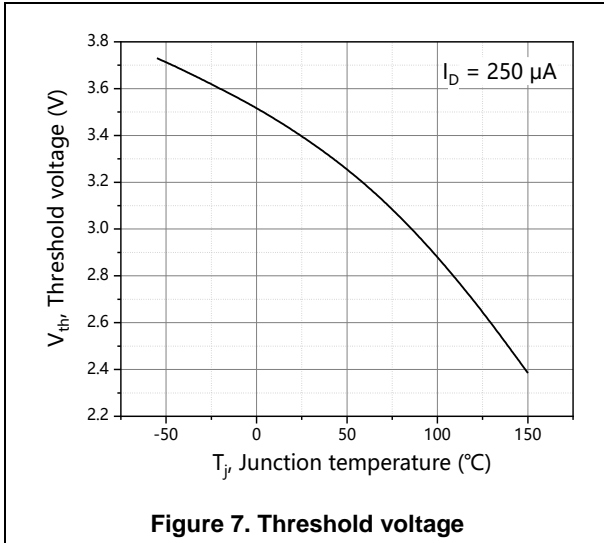


Figure 6. Drain-source on-state resistance



Test circuits and waveforms

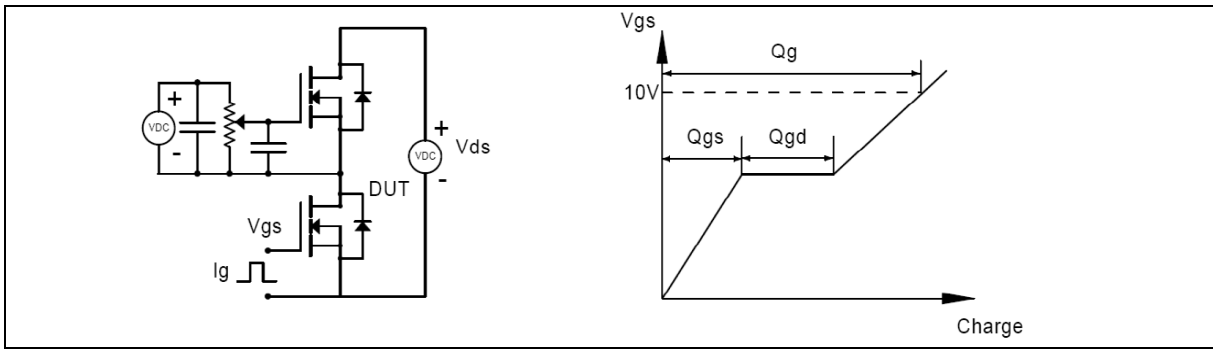


Figure 1. Gate charge test circuit & waveform

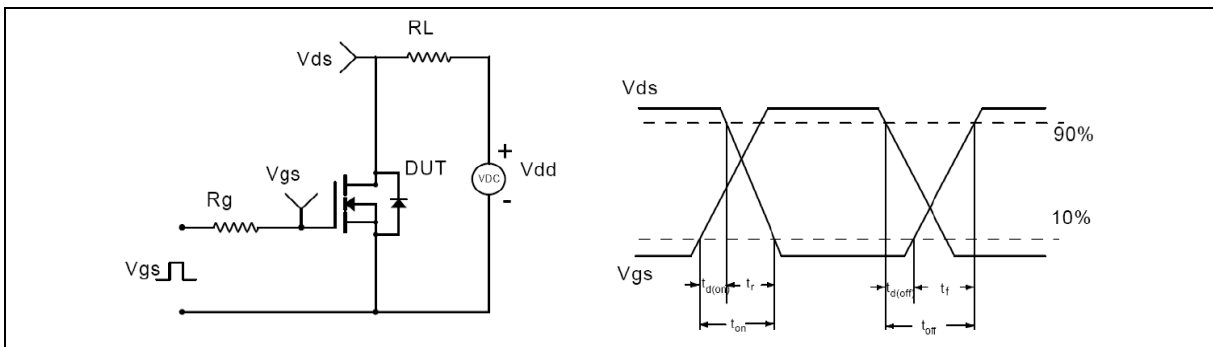


Figure 2. Switching time test circuit & waveforms

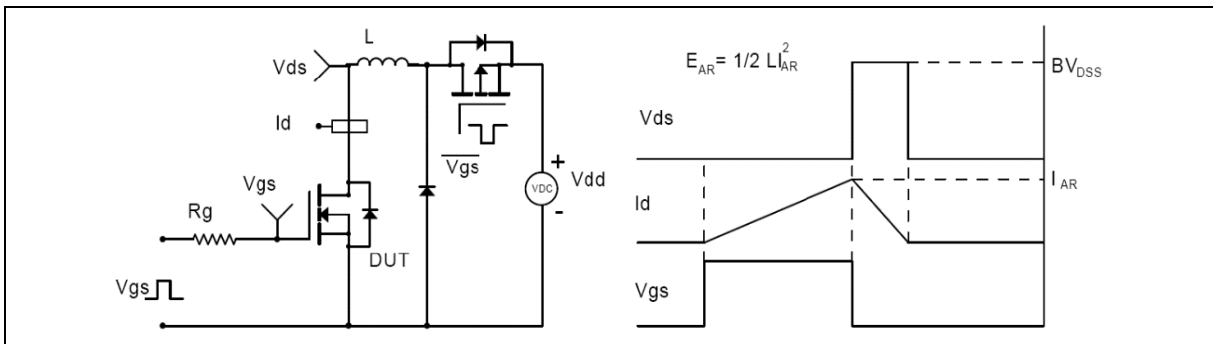


Figure 3. Unclamped inductive switching (UIS) test circuit & waveforms

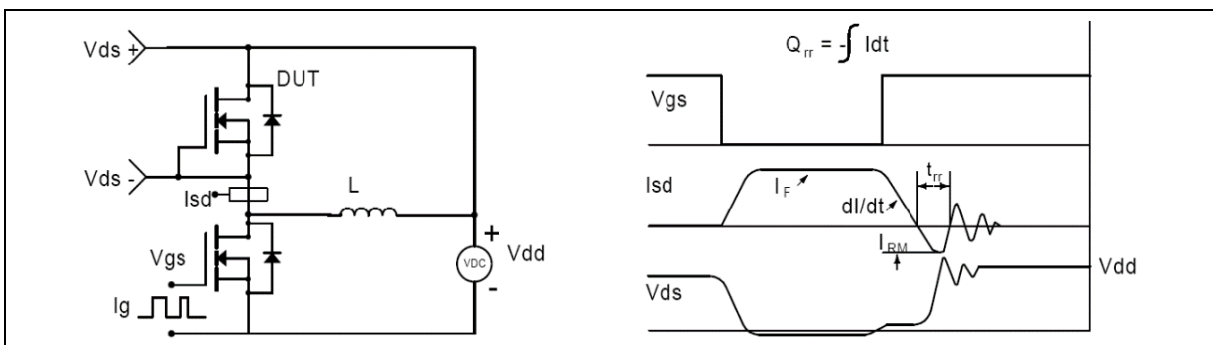
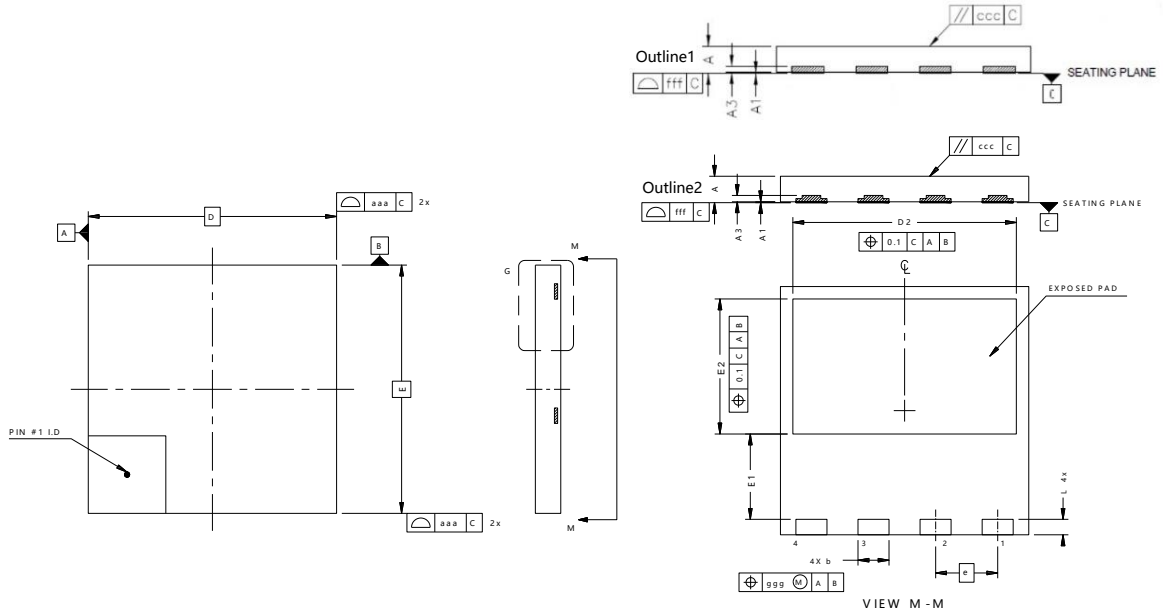


Figure 4. Diode reverse recovery test circuit & waveforms

Package Information



Symbol	mm	
	Min	Max
A	0.75	0.95
A1	0.00	0.05
A3	0.10	0.30
b	0.90	1.10
D	7.90	8.10
E	7.90	8.10
D2	7.10	7.30
E1	2.65	2.85
E2	4.25	4.45
e	2.0 BSC	
L	0.40	0.60
aaa	0.1	
ggg	0.05	
ccc	0.05	
fff	0.05	

Version 1: PDFN 8x8-S package outline dimension

Ordering Information

Package Type	Units/ Reel	Reels/ Inner Box	Units/ Inner Box	Inner Boxes/ Carton Box	Units/ Carton Box
PDFN 8x8-S	2500	1	2500	10	25000

Product Information

Product	Package	Pb Free	RoHS	Halogen Free
OSS65R240JF	PDFN 8x8	yes	yes	yes

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